

BF545A; BF545B; BF545C

N-channel silicon junction field-effect transistors Rev. 4 — 15 September 2011 Proc

Product data sheet

Product profile

1.1 General description

N-channel symmetrical silicon junction field-effect transistors in a SOT23 package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Low leakage level (typ. 500 fA)
- High gain
- Low cut-off voltage (max. 2.2 V for BF545A).

1.3 Applications

- Impedance converters in e.g. electret microphones and infra-red detectors
- VHF amplifiers in oscillators and mixers.

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage		-	-	±30	V
V_{GSoff}	gate-source cut-off voltage	$I_D = 1 \mu A; V_{DS} = 15 V$	-0.4	-	-7.8	V
I _{DSS}	drain current	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$				
		BF545A	2	-	6.5	mA
		BF545B	6	-	15	mA
		BF545C	12	-	25	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	-	-	250	mW
y _{fs}	forward transfer admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	3	-	6.5	mS



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	source (s)		
2	drain (d)		g → d s
3	gate (g)	1 7 72	sym054

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BF545A	-	plastic surface mounted package; 3 leads	SOT23			
BF545B						
BF545C						

4. Marking

Table 4. Marking

Type number	Marking code ^[1]
BF545A	20*
BF545B	21*
BF545C	22*

^{[1] * =} p: made in Hong Kong.

^{* =} t: made in Malaysia.

^{* =} W: made in China.

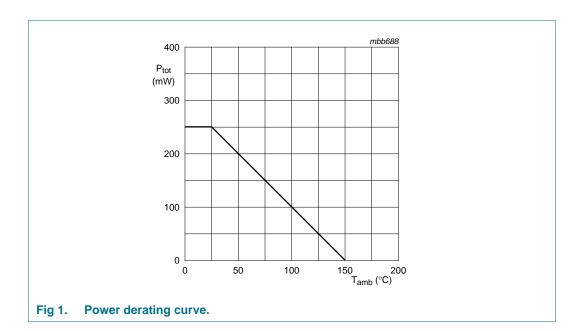
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	±30	V
V_{GSO}	gate-source voltage	open drain	-	-30	V
V_{GDO}	gate-drain voltage (DC)	open source	-	-30	V
I_{G}	forward gate current (DC)		-	10	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Тур	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u>	500	K/W

^[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².

7. Static characteristics

Table 7. Static characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)GSS}	gate-source breakdown voltage	$I_G = -1 \mu A; V_{DS} = 0 V$	-30	-	-	V
V_{GSoff}	gate-source cut-off voltage	$I_D = 200 \mu A; V_{DS} = 15 V$				
		BF545A	-0.4	-	-2.2	V
		BF545B	-1.6	-	-3.8	V
		BF545C	-3.2	-	-7.8	V
		$I_D = 1 \mu A; V_{DS} = 15 V$	-0.4	-	-7.5	V
I _{DSS}	drain current	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$				
		BF545A	2	-	6.5	mΑ
		BF545B	6	-	15	mΑ
		BF545C	12	-	25	mΑ
I _{GSS}	gate-source leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-0.5	-1000	рА
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V};$ $T_j = 125 ^{\circ}\text{C}$	-	-	-100	nA
y _{fs}	forward transfer admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	3	-	6.5	mS
y _{os}	common source output admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	40	-	μS

8. Dynamic characteristics

Table 8. Dynamic characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}$				
		$V_{GS} = -10 \text{ V}$	-	1.7	-	pF
		$V_{GS} = 0 V$	-	3	-	pF
C _{rss}	reverse transfer capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}$				
		V _{GS} = −10 V	-	0.8	-	pF
		$V_{GS} = 0 V$	-	0.9	-	pF
gis	common source input conductance	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
		f = 100 MHz	-	15	-	μS
		f = 450 MHz	-	300	-	μS
g _{fs}	common source transfer conductance	$V_{DS} = 10 \text{ V}; I_{D} = 1 \text{ mA}$				
		f = 100 MHz	-	2	-	mS
		f = 450 MHz	-	1.8	-	mS
g _{rs}	common source reverse	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
	conductance	f = 100 MHz	-	-6	-	μS
		f = 450 MHz	-	-40	-	μS
g _{os}	common source output	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
	conductance	f = 100 MHz	-	30	-	μS
		f = 450 MHz	-	60	-	μS

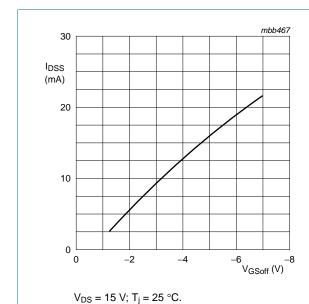
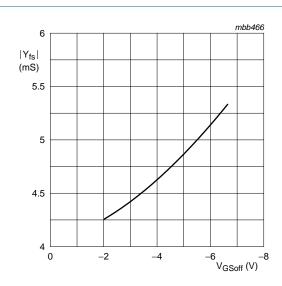
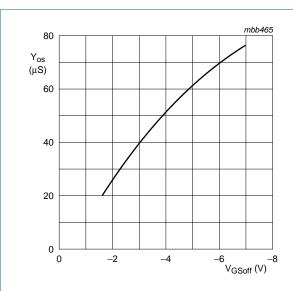


Fig 2. Drain current as a function of gate-source cut-off voltage; typical values.



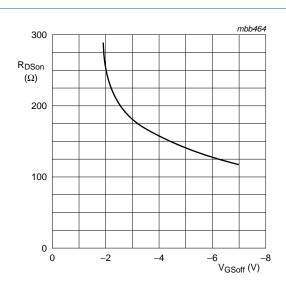
 V_{DS} = 15 V; V_{GS} = 0 V; T_j = 25 °C.

Fig 3. Forward transfer admittance as a function of gate-source cut-off voltage; typical values.



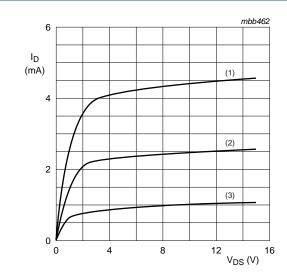
 V_{DS} = 15 V; V_{GS} = 0 V; T_j = 25 °C.

Fig 4. Common-source output admittance as a function of gate-source cut-off voltage; typical values.



 V_{DS} = 100 mV; V_{GS} = 0 V; T_j = 25 °C.

Fig 5. Drain-source on-resistance as a function of gate-source cut-off voltage; typical values.

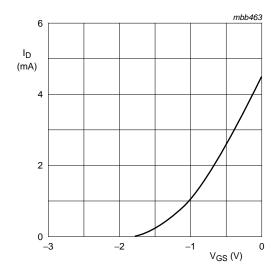


BF545A

 $T_i = 25 \, ^{\circ}C$.

- (1) $V_{GS} = 0 V$.
- (2) $V_{GS} = -0.5 \text{ V}.$
- (3) $V_{GS} = -1.0 \text{ V}.$

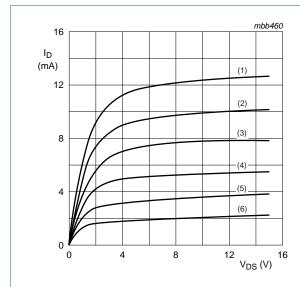
Fig 6. Typical output characteristics.



BF545A

 $V_{DS} = 15 \text{ V}; T_i = 25 ^{\circ}\text{C}.$

Fig 7. Typical input characteristics.

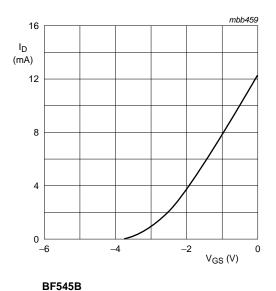


BF545B

$$T_i = 25 \, ^{\circ}C$$
.

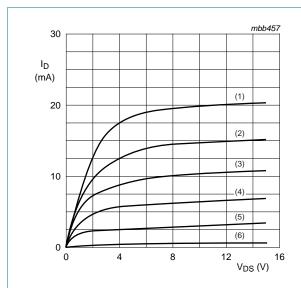
- (1) $V_{GS} = 0 V$.
- (2) $V_{GS} = -0.5 \text{ V}.$
- (3) $V_{GS} = -1.0 \text{ V}.$
- (4) $V_{GS} = -1.5 \text{ V}.$
- (5) $V_{GS} = -2.0 \text{ V}.$
- (6) $V_{GS} = -2.5 \text{ V}.$

Fig 8. Typical output characteristics.



 $V_{DS} = 15 \text{ V}; T_i = 25 \text{ }^{\circ}\text{C}.$

Fig 9. Typical input characteristics.

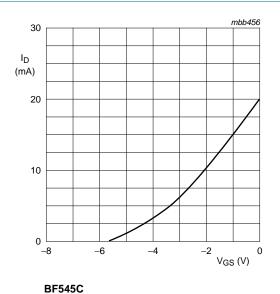


BF545C

 $T_j = 25 \, ^{\circ}C$.

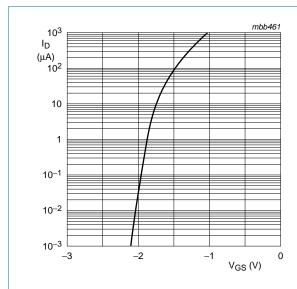
- (1) $V_{GS} = 0 V$.
- (2) $V_{GS} = -1.0 \text{ V}.$
- (3) $V_{GS} = -2.0 \text{ V}.$
- (4) $V_{GS} = -3.0 \text{ V}.$
- (5) $V_{GS} = -4.0 \text{ V}.$
- (6) $V_{GS} = -5.0 \text{ V}.$

Fig 10. Typical output characteristics.



 $V_{DS} = 15 \text{ V}; T_j = 25 ^{\circ}\text{C}.$

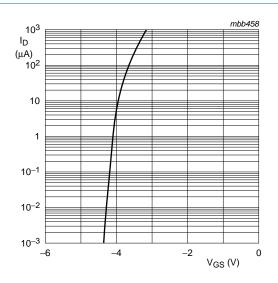
Fig 11. Typical input characteristics.



BF545A

 $V_{DS} = 15 \text{ V}; T_i = 25 \text{ }^{\circ}\text{C}.$

Fig 12. Drain current as a function of gate-source voltage; typical values.



BF545B

 -10^{2}

 I_G

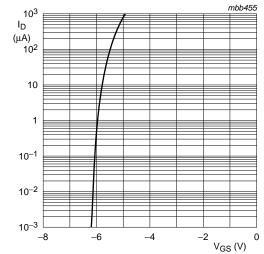
(pA) -10

 -10^{-1}

 -10^{-2}

 $V_{DS} = 15 \text{ V}; T_i = 25 \text{ }^{\circ}\text{C}.$

Fig 13. Drain current as a function of gate-source voltage; typical values.



BF545C

 $V_{DS} = 15 \text{ V}; T_i = 25 ^{\circ}\text{C}.$





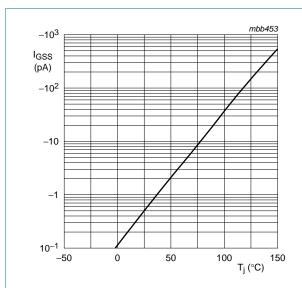
(1) $I_D = 10 \text{ mA}.$

(4)

- (2) $I_D = 1 \text{ mA}.$
- (3) $I_D = 0.1 \text{ mA}.$
- (4) I_{GSS}.

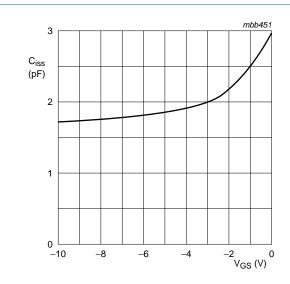
Fig 15. Gate current as a function of drain-gate voltage; typical values.

Fig 14. Drain current as a function of gate-source voltage; typical values.



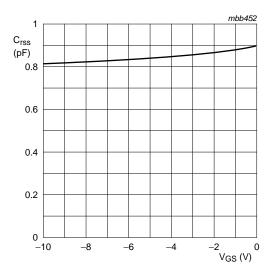
 $V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}.$

Fig 16. Gate current as a function of junction temperature; typical values.



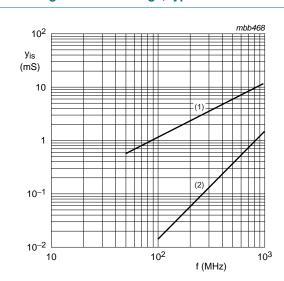
 $V_{DS} = 15 \text{ V}; T_i = 25 ^{\circ}\text{C}.$

Fig 18. Typical input capacitance.



$$V_{DS} = 15 \text{ V}; T_i = 25 \text{ }^{\circ}\text{C}.$$

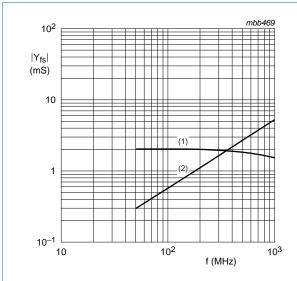
Fig 17. Reverse transfer capacitance as a function of gate-source voltage; typical values.



$$V_{DS} = 10 \text{ V}; I_{D} = 1 \text{ mA}; T_{amb} = 25 \text{ °C}.$$

- (1) b_{is}.
- (2) g_{is}.

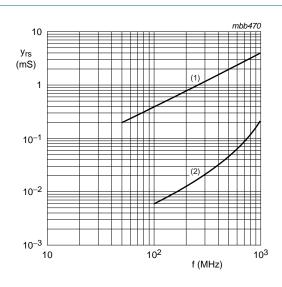
Fig 19. Common-source input admittance; typical values.



 V_{DS} = 10 V; I_D = 1 mA; T_{amb} = 25 °C.

- (1) g_{fs}
- (2) $-b_{fs}$.

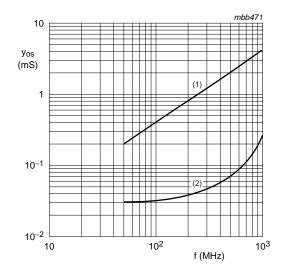
Fig 20. Common-source forward transfer admittance; typical values.



 $V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}.$

- -b_{rs}.
- $(2) \quad -g_{rs}.$

Fig 21. Common-source reverse transfer admittance; typical values.



 V_{DS} = 10 V; I_D = 1 mA; T_{amb} = 25 °C.

- (1) b_{os}.
- (2) g_{os}.

Fig 22. Common-source output admittance; typical values.

9. Package outline

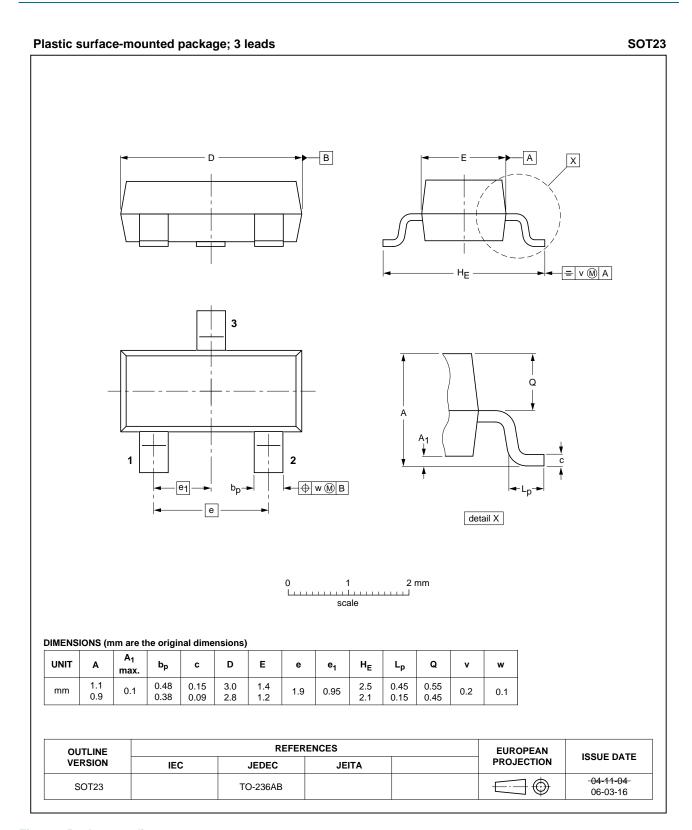


Fig 23. Package outline.

BF545A_BF545B_BF545C

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BF545A_BF545B_BF545C v.4	20110915	Product data sheet	-	BF545A_BF545B_BF545C v.3
Modifications:		of this data sheet has be of NXP Semiconductors.	•	comply with the new identity
	 Legal texts 	have been adapted to th	ne new company r	name where appropriate.
	 Package ou 	ıtline drawings have bee	n updated to the I	atest version.
BF545A_BF545B_BF545C v.3 (9397 750 13391)	20040805	Product data sheet	-	BF545A-B-C v.2
BF545A-B-C v.2	19960729	Product specification	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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N-channel silicon junction field-effect transistors)

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12. Contact information

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For sales office addresses, please send an email to: salesaddresses@nxp.com

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.